Supplementary Information

for

Ligand Assisted Growth of Perovskite Single Crystals with Low Defect Density

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Supplementary Table 1. Dark current drift and resistivity of the as-grown MAPbI₃ crystals with DPSI in Fig. S6 without any surface treatment.

Electric field	Dark current	Resistivity	Current drift
$(V \text{ cm}^{-1})$	$(nA cm^{-2})$	$(\Omega \text{ cm})$	$(nA cm^{-1} v^{-1}s^{-1})$
50	27.2	1.84×10^{9}	5.95 ×10 ⁻⁵
125	48.8	2.56×10^{9}	$2.45 imes 10^{-5}$
250	80	3.13×10^{9}	$1.48 imes 10^{-5}$

Supplementary Table 2. Summary of the sensitivity and lowest detectable dose rate of different perovskite X-ray direct and indirect radiation detectors.

	Perovskite	X-ray	Sensitivity	Lowest	Dark	References
	composition	energy	(uC Cu ⁻¹ air	detectable	current	
		(keV	$(\mu C Gy alf cm^{-2})$	dose rate	drift	
		or	em)	$(\mu Gy air s^{-1})$	(nA cm ⁻¹	
Indirect		kVp)			$v^{-1} s^{-1}$)	
conversion	MAPhCl ₂	50		0.1147		Δ
(Scintillators)	single crystal	50		0.1147		-
		20		0.1015		~
	Ru ₂ CuBr ₃	30		0.1215		5
	Rb ₃ Bi ₂ I ₉	50	159.7	0.00832	1.82×10^{-7}	6
			(1 V bias)			
			(1 v blus)			
	MAPbBr ₃	8	80	0.5		1
	single crystal					
	MAPbBr ₃ /Si	8	2.1×10^4	0.036	1.2×10 ⁻³	3
	integration					
	MAPbBr _x Cl _{3-x}	8	8.4×10^4	0.0076		2
	single crystal					
	MAPbBr ₃		184.6			7
	single crystal		101.0			,
	(oil growth)					
	(NH4)2BisI2		8.2×10^{3}	0.055		8
	(11114)3D1219-		0.2 ×10	0.055		0

	2D single crystal					
Direct	BiOBr passivated Cs ₂ AgBiBr ₆	50	250 (0.5V μm ⁻¹)	0.0953	7.4×10 ⁻⁵	9
conversion (Radiation	wafer film					
detectors)	Cs ₂ AgBiBr ₆	30	105	0.0597		10
	single crystal					
	MAPbI ₃ cuboid shape crystal		968.9			11
	(GMA)MAPbI ₃	8	2.3×10^4	0.0169		12
	single crystal		(5V bias)			
	MAPbI ₃	70	2.527×10^{3}		1.7×10 ⁻³	13
	sintered water		(200V bias)			
	MAPbI ₃	40	1.22×10^{5}	2.54		14
	pressed sinter		(10 V bias)			
	Cs ₃ Bi ₂ I ₉	40	1.652×10^{3}	0.130		15
	Single crystal		(60 V bias)			
	(F-PEA) ₂ PbI ₄	120	3.402×10^3	0.023	4.9×10 ⁻⁸	16
	2D single crystal		(200V bias)			
	MAPbI ₃	100	1.1×10^4			17
	(printable film)					
	MAPbI ₃ (Cl) in	60	8,696±228			
	membrane	100	1.44×10^4			18
			(20V bias)			
	MAPbI ₃ thin single crystal	50	7.0×10 ³	0.0015		19
	(co-planar)		(5V bias)			
			2.1×10 ⁵	0.00234	6.58×10 ⁻⁶	
		8	(10V bias)			

		2.8×10 ⁵ (20V bias)		1.3×10 ⁻⁵	
MAPbI ₃ single crystal with ligand-assisted	60	2.9×10 ⁶ (100V bias)	0.0057	4.7×10 ⁻⁵	This work
	100	6.51×10 ⁵ (100V bias)			
	120	1.04×10 ⁶ (100V bias)			



Supplementary Fig. 1. a) XRD pattern of different facets of the diamond-shaped crystal shown in Fig.1A. **b**, **c**) photos of the two crystals grown in 10% DPSI added, and the facet angles were measured.



Supplementary Fig. 2. Crystal growth behavior with ligand regulation after seeding. a) Scheme and photos of crystal growth process after seeding dodecahedral crystals (pristine MAPbI₃ crystal) in precursor solutions w/o and with DPSI. **b**) The crystal growth rate comparison of the crystals w/o and with DPSI at different temperature after seeding. The scale bar is 5 mm.



Supplementary Fig. 3. Crystal growth behavior of MAPbBr₃ single crystals with adding DPSI in precursor. a, b) Scheme and photograph of the crystals growth rate comparison w/o and with DPSI.



Supplementary Fig. 4. Photographs of MAPbI₃ single crystals grown with molar ratio of 10% DPSI in different dimensional sizes: a-c) some large crystals above 1 cm in length and d-f) some small crystals.



Supplementary Fig. 5. Crystal quality improvement of MAPbBr₃ single crystals with DPSI in precursor solution. Electron and hole carrier mobility of the crystals grown **a**, **b**) w/o and **c**, **d**) with DPSI, respectively.



Supplementary Fig. 6. Dark current drift of a non-encapsulated device based on MAPbI₃ single crystal grown with DPSI under different applied electric field of 50 V cm⁻¹, 125 V cm⁻¹ and 250 V cm⁻¹. The crystal thickness was 4 mm without any surface treatment before device fabrication, and the photograph of the crystal was shown in Supplementary Fig. 4c.



Supplementary Fig. 7. Performance of the X-ray detector under soft X-ray energy with energy of 8 keV. a) Dark current drift in air without encapsulation, and b) X-ray sensitivity measurement excited by 8 keV X-ray beam energy under bias of -5 V, -10 V and -20 V. The

crystal thickness was 3.7 mm, which is the same crystal in Fig. 4b and its photograph is shown in Supplementary Fig. 4a.



Supplementary Fig. 8. Simulated X-ray energy spectrum of the source by SPEKTR 3.0 with 21 mm Al filter at **a**) 60 kVp, **b**) 100 kVp and **c**) 120 kVp.

Supplementary References

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